

**FEATURES**

- Square Active Area
- Round 4-Pin Package
- Ideal for Electron Detection

**Electro-Optical Characteristics at 25 °C**

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	24.01 mm x 24.01 mm		576.5		mm <sup>2</sup>
Responsivity	(see graphs on next page)				
Shunt Resistance, Rsh	@ ±10 mV	5	50		MΩ
Reverse Breakdown Voltage, V <sub>R</sub>	I <sub>R</sub> = 1 μA	5			Volts
Capacitance, C	V <sub>R</sub> = 0 V		5	15	nF
Rise Time, tr	V <sub>R</sub> = 10 V, R <sub>L</sub> = 50 Ω			50	usec

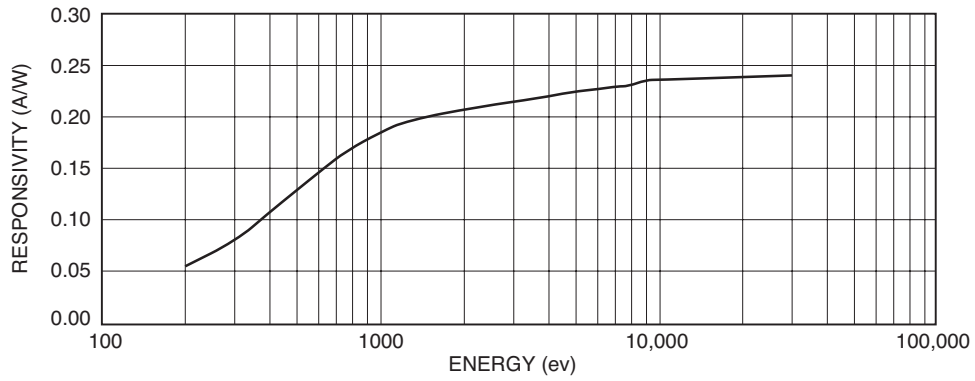
**Thermal Parameters**

Storage and Operating Temperature Range	Units
Ambient <sup>1</sup>	-10° to 40°C
Nitrogen or Vacuum	-20°C to 80°C
Lead Soldering Temperature <sup>2</sup>	260°C

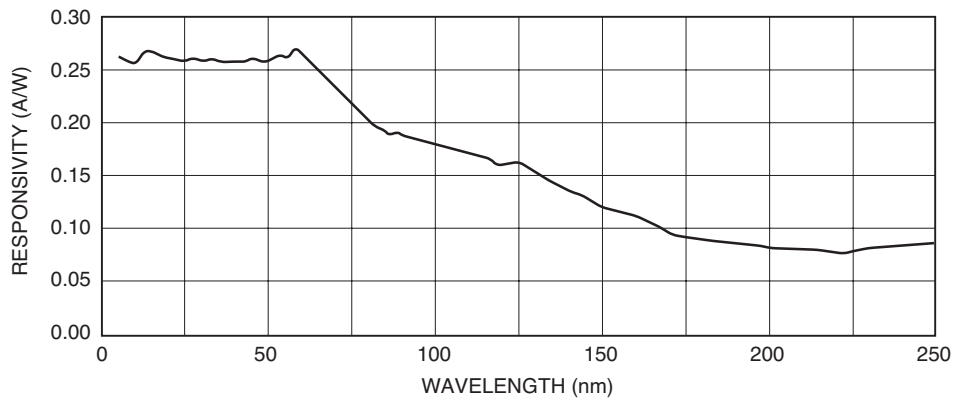
<sup>1</sup> Temperatures exceeding these parameters may create oxide growth on the active area. Over time responsivity to low energy radiation and wavelengths below 150 nm will be compromised.

<sup>2</sup> 0.080" from case for 10 seconds.

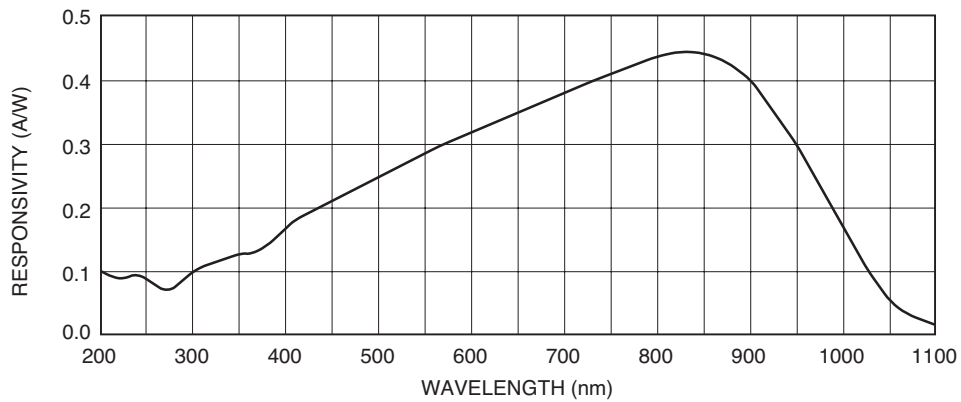
**Typical Electron Response**



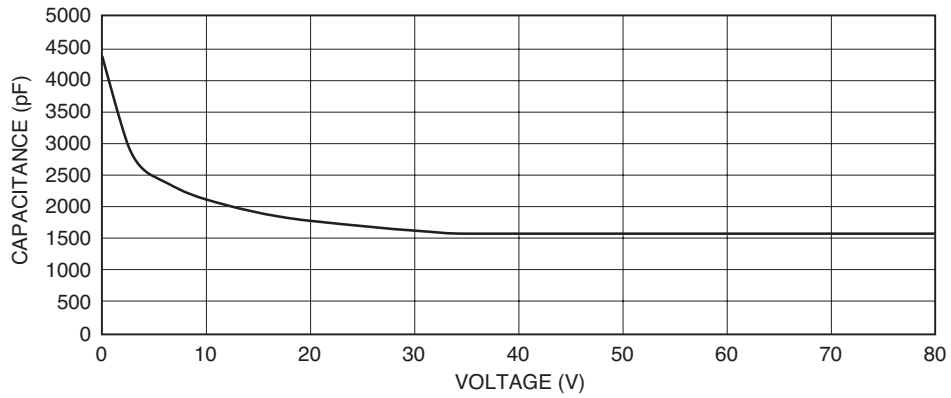
**Typical EUV-UV Photon Response**



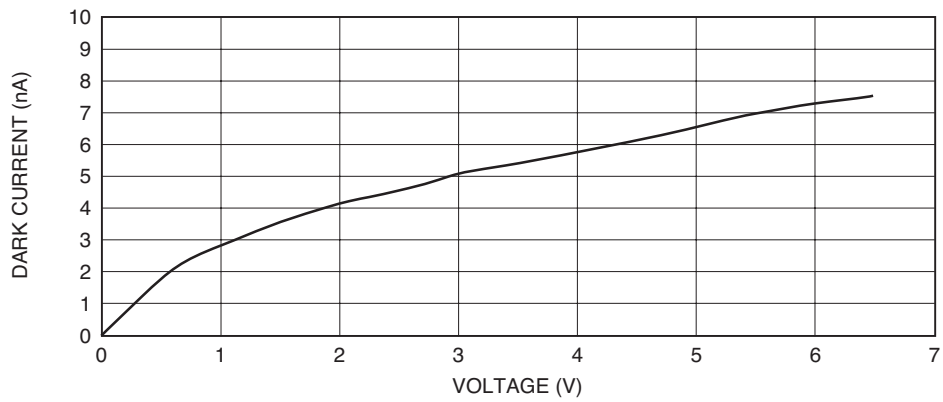
**Typical UV-VIS-NIR Photon Responsivity**



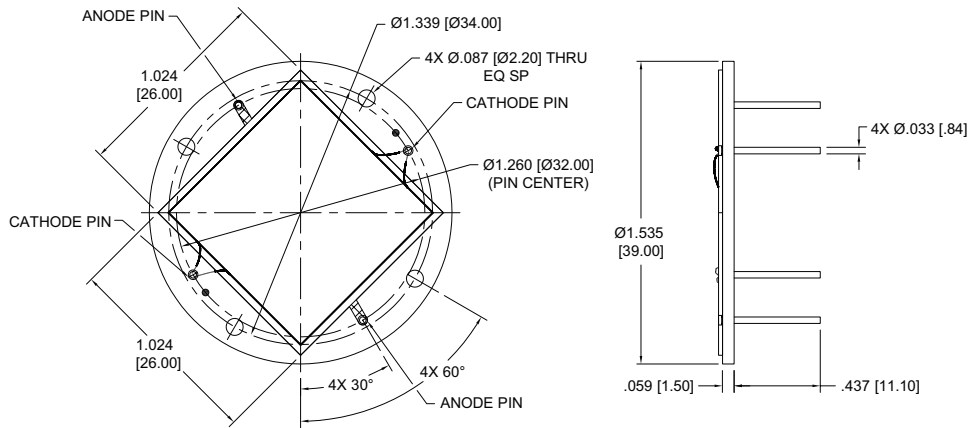
**Capacitance vs. Voltage**



**Dark Current vs. Voltage**



**Package Information**



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.

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